

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI BLV32F** is Designed for in linear v.h.f. amplifiers of television transmitters and transporters.

**FEATURES:**

- Diffused emitter ballasting resistors
- $P_G = 16$  dB at 10 W/224 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	4.0 A
$V_{CBO}$	60 V
$V_{CEO}$	32 V
$V_{CES}$	60 V
$V_{EBO}$	4.0 V
$P_{DISS}$	82 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	2.1 $^\circ C/W$

**PACKAGE STYLE .500 6L FLG**

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.150/3.43	.160/4.06
B	.045/1.14	
C	.210/5.33	.220/5.59
D	.835/21.21	.865/21.97
E	.200/5.08	.210/5.33
F	.490/12.45	.510/12.95
G	.003/0.08	.007/0.18
H	.125/3.18	
I	.720/18.29	.730/18.54
J	.970/24.64	.980/24.89
K	.095/2.41	.105/2.67
L	.150/3.81	.170/4.32
M	.280/7.11	

1= Collector 2= Base 3 and 4= Emitter

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 100$ mA		32			V
$BV_{CES}$	$I_C = 15$ mA		60			V
$BV_{EBO}$	$I_E = 10$ mA		4.0			V
$I_{CES}$	$V_{CE} = 32$ V				5.0	mA
$h_{FE}$	$V_{CE} = 25$ V	$I_C = 1.6$ A	20		120	---
$C_C$	$V_{CB} = 25$ V	$f = 1.0$ MHz		50		pF
$P_G$	$V_{CE} = 25$ V	$P_{OUT} = 10$ W	$f = 224$ MHz	16		dB